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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/623788
	Filing Date	July 21, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2811
	Examiner Name	Unknown
Sheet 1 of 7	Attorney Docket No: 1303.109US1	

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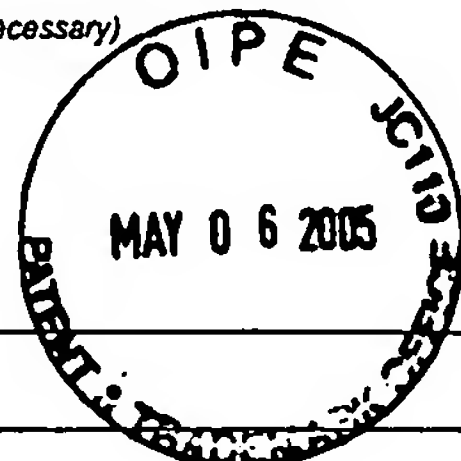
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Application Number	10/623,788
Filing Date	July 21, 2003
First Named Inventor	Forbes, Leonard
Group Art Unit	2811
Examiner Name	Unknown

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Attorney Docket No: 1303.109US1

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	Application Number	10/623,788
	Filing Date	July 21, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2811
	Examiner Name	Unknown
Sheet 2 of 2	Attorney Docket No: 1303.109US1	

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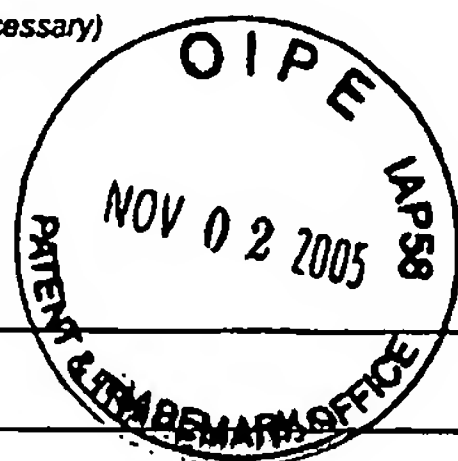
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First Named Inventor	Forbes, Leonard
Group Art Unit	2822
Examiner Name	Perkins, Pamela

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Attorney Docket No: 1303.109US1

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